

Hyperfast Rectifier, 8 A FRED Pt[®]





VS-8ETH06FP-N3

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS			
I _{F(AV)}	8 A		
V _R	600 V		
V _F at I _F	1.3 V		
t _{rr} typ.	18 ns		
T _J max.	175 °C		
Package	TO-220 FullPAK 2L		
Circuit configuration	Single		

FEATURES

- · Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{BMS})
- Designed and gualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: TO-FullPAK 2L

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Repetitive peak reverse voltage	V _{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	T _C = 108 °C	8		
Non-repetitive peak surge current	I _{FSM}		100	А	
Repetitive peak forward current	I _{FM}		16		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-		
Converd voltege	V	I _F = 8 A	-	2.0	2.4	V	
Forward voltage V _F		I _F = 8 A, T _J = 150 °C	-	1.3	1.8		
Deverage la clus es environt		$V_{\rm R} = V_{\rm R}$ rated	-	0.03	50		
Reverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	55	500	μA	
Junction capacitance	CT	V _R = 600 V - 17 -		pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 -		nH			

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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	18	22	
Reverse recovery time	t _{rr}	$I_F = 8 \text{ A}, \ dI_F/dt = 100$	I _F = 8 A, dI _F /dt = 100 A/μs, V _R = 30 V		20	25	ns
neverse recovery time	۲r	T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/μs V _B = 390 V	-	25	-	115
		T _J = 125 °C		-	40	-	
Poak rocovony ourront	Peak recovery current I _{RRM}	T _J = 25 °C		-	2.4	-	A
Feak recovery current		T _J = 125 °C		-	4.8	-	
	Q _{rr}	T _J = 25 °C	v _R – 000 v	-	25	-	nC
Reverse recovery charge		T _J = 125 °C		-	120	-	ne
Reverse recovery time	t _{rr}	T _J = 125 °C	I _F = 8 A	-	33	-	ns
Peak recovery current	I _{RRM}		dI _F /dt = 600 A/µs V _R = 390 V	-	12	-	А
Reverse recovery charge	Q _{rr}			-	220	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction-to-case	R _{thJC}		-	3.4	4.3	°C/W
Thermal resistance, junction-to-ambient per leg	R _{thJA}	Typical socket mount	-	-	70	
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-	
Weight			-	2.0	-	g
weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220 FullPAK 2L	8ETH06FP			

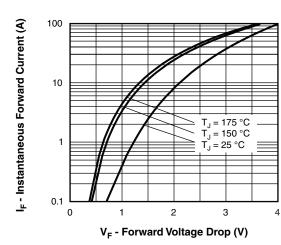


Fig. 1 - Typical Forward Voltage Drop Characteristics

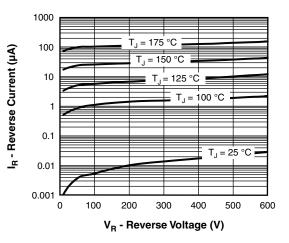


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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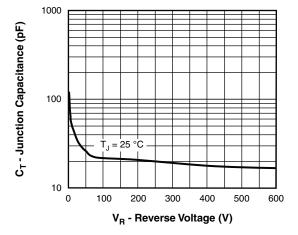


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

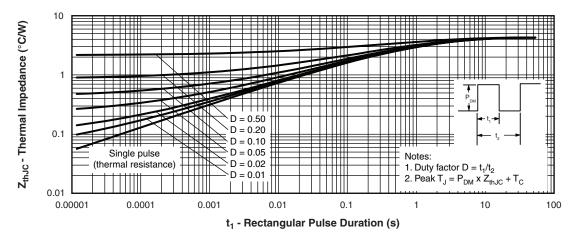
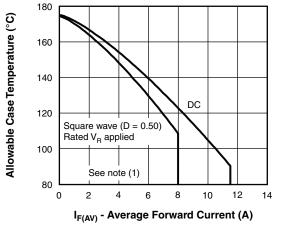
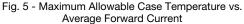


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

Average Power Loss (W)





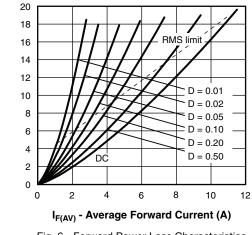


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

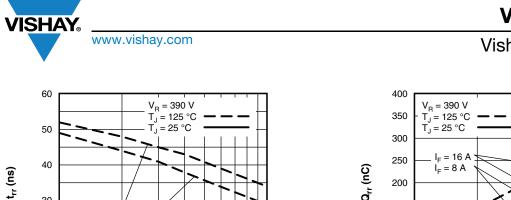
 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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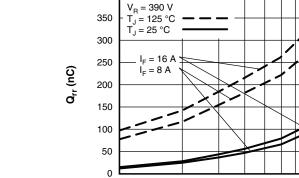
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1000



100

dl_F/dt (A/µs) Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

30

20

10

100

 $I_{F} = 16 \text{ A}$

Z $I_F = 8 A$



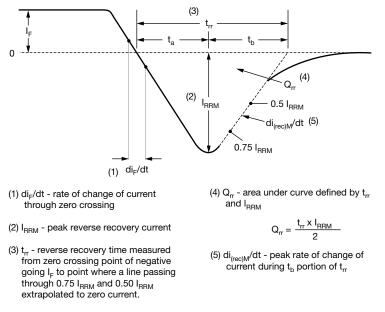


Fig. 9 - Reverse Recovery Waveform and Definitions

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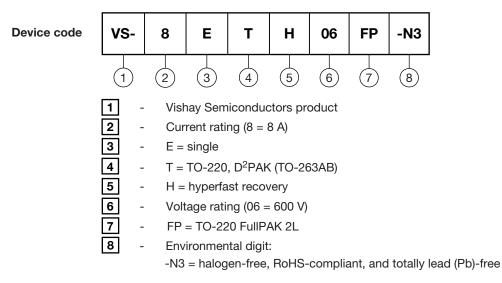
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ORDERING INFORMATION TABLE



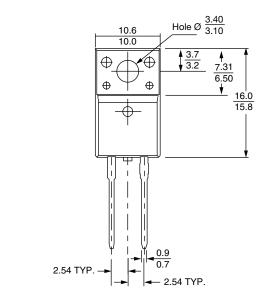
ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-8ETH06FP-N3	50	1000	Antistatic plastic tube	

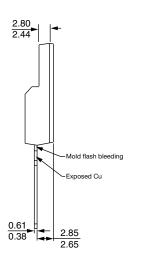
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96157
Part marking information	www.vishay.com/doc?95392

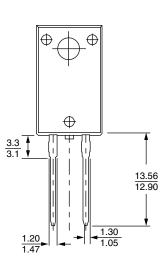


2L TO-220 FullPAK

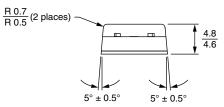
DIMENSIONS in millimeters







Bottom view





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